



Product Summary

BV _{DSS}	RDS(ON) Max	I _{D Max} T _A = +25°C
60V	16mΩ @ V _{GS} = 10V	8.9A
007	27mΩ @ V _{GS} = 4.5V	6.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Adaptor Switch
- Notebook PC

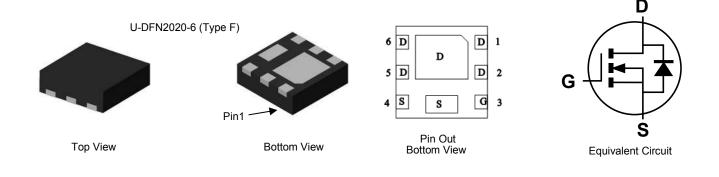
60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity per Reel
DMT6016LFDF-7	Т6	7	3000
DMT6016LFDF-13	Т6	13	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

Site 1:



T6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Year	2013		. 1	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	А			G	Н	I	J	K	L	М	N	0	Р
Month	Ja	n	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1		2	3	4	5	6	7	8	9	0	N	D
							T6 =	Product T	ype Markin	g Code			
te Code K					T6 ●	2	YW2 Y = W = X =	K = Date C Year (ex: H Week (ex: Internal co	ode Markin I = 2020) a = week 2 de (ex: U =	g 27; z repres Monday)			
te Code K Year	iey 202	20	202	1	T6 • 2022	X M J	YWX Y = 7 W =	K = Date C Year (ex: H Week (ex: Internal co	ode Markin I = 2020) a = week 2 de (ex: U = 2025	g 27; z repres	ents week		3) 2028
			<u>202</u> 1	1	•		YW2 Y = W = X =	K = Date C Year (ex: H Week (ex: Internal co 24	ode Markin I = 2020) a = week 2 de (ex: U =	g 27; z repres Monday)		27	
Year	202				•	2023	YWX Y = 7 W = X = 20	K = Date C Year (ex: H Week (ex: Internal co 24	ode Markin I = 2020) a = week 2 de (ex: U = 2025	g 27; z repres Monday) 2026	202	27	2028

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	Х	Y	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Dania Current (Note C))/ - 40)/	Steady State	T _A = +25°C T _A = +70°C	ID	8.9 7.1	A
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C T _A = +70°C	ID	11.1 8.9	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	%)	•	I _{DM}	60	A
Maximum Body Diode Continuous Current			ls	2.2	A
Avalanche Current (Note 7) L = 0.1mH		I _{AS}	15.3	A	
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	11.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Dowor Dissinction (Note E)	T _A = +25°C	Р	0.82	W
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.52	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Р	153	°C/W
memar Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	97	C/W
Total Power Dissipation (Note 6)	T _A = +25°C	6	1.9	W
Total Power Dissipation (Note 6)	T _A = +70°C	PD	1.2	
Thermal Desistance, Junction to Ambient (Note 6)	Steady State	P	66	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _{0JA}	42	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{ejc}	14.7	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

2			1	1		1
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					-	1
Drain-Source Breakdown Voltage	BV _{DSS}	60			V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	IDSS	_		1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}		—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	V_{DS} = V_{GS} , I_D = 250 μ A
Static Drain-Source On-Resistance	D		12.2	16	mΩ	V _{GS} = 10V, I _D = 10A
	R _{DS(ON)}		17.2	27	11152	V_{GS} = 4.5V, I_{D} = 6A
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}		864	—		
Output Capacitance	C _{oss}		282	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	27.1	—		1 - 1.000112
Gate Resistance	Rg	_	1.35	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg		17	_		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.4	—	nC	$V_{DS} = 30V, I_{D} = 10A$
Gate-Source Charge	Q _{gs}	_	3.1	_	no	$v_{\rm DS} = 30$ V, $I_{\rm D} = 10$ A
Gate-Drain Charge	Q _{gd}	_	4.3	_		
Turn-On Delay Time	t _{D(ON)}	_	3.4	_		
Turn-On Rise Time	t _R	_	5.2	_	nS	$V_{GS} = 10V, V_{DD} = 30V, R_{g} = 6\Omega,$
Turn-Off Delay Time	t _{D(OFF)}	_	12.9	_	115	I _D = 10A
Turn-Off Fall Time	t _F	_	6.8	_		
Body Diode Reverse Recovery Time	t _{RR}	_	22		nS	I _S = 10A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}		11.1		nC	I _S = 10A, dl/dt = 100A/µs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

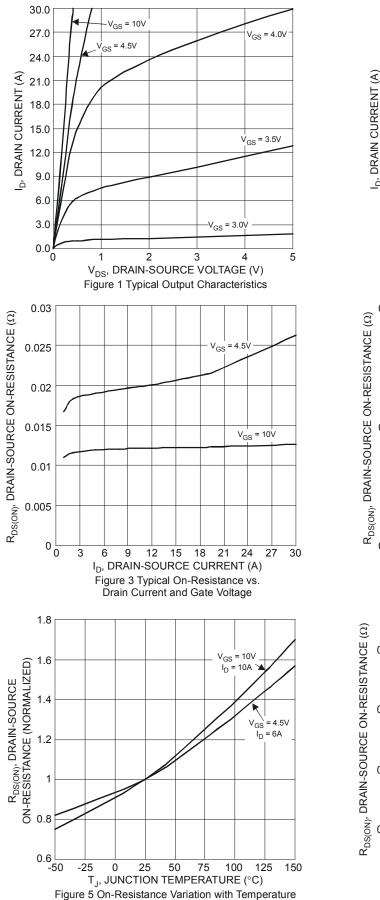
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







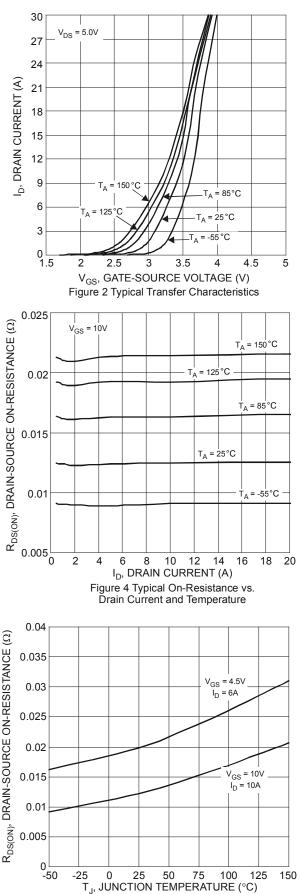
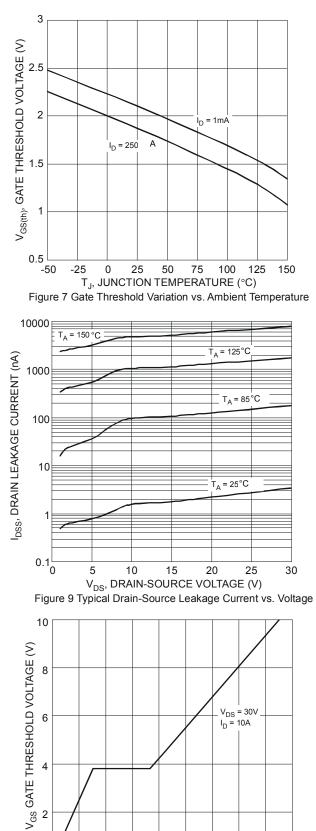
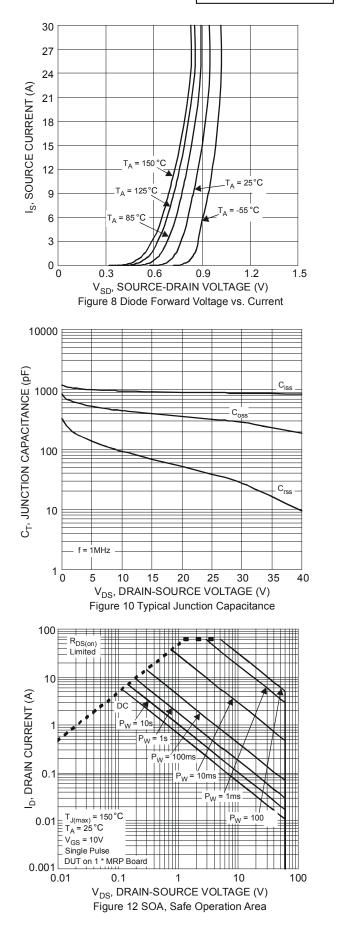


Figure 6 On-Resistance Variation with Temperature









2

4

6

8 10 12

Q_g, TOTAL GATE CHARGE (nC)

Figure 11 Gate Charge

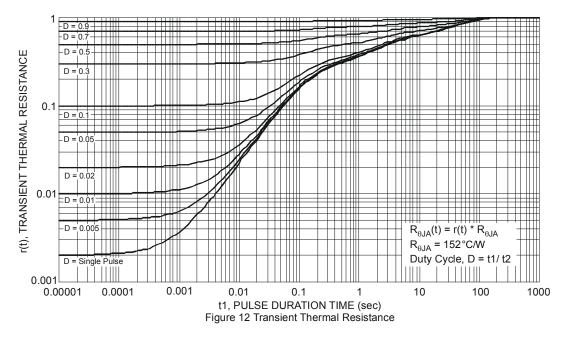
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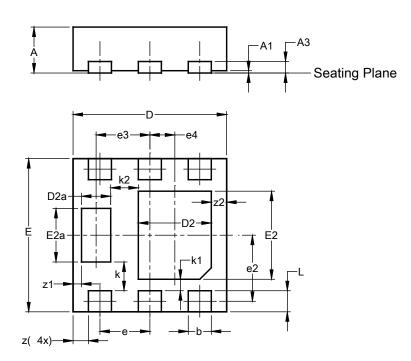






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

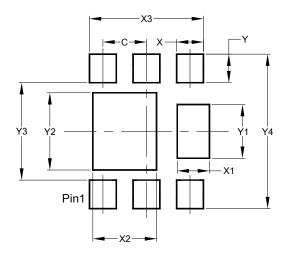


	U-DFN	2020-6	
		be F)	
Dim	Min	Мах	Тур
Α	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
е		0.65 BS	С
e2	0).863 BS	SC
e3		0.70 BS	С
e4	0).325 BS	SC
k		0.37 BS	С
k1		0.15 BS	С
k2		0.36 BS	С
L	0.225	0.325	0.275
z		0.20 BS	С
z1	0).110 BS	SC
z2		0.20 BS	С
All C)imens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dimensions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

U-DFN2020-6 (Type F)



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